QS8K21

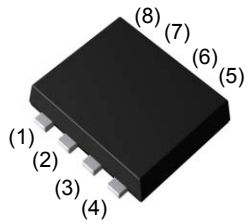
Nch 45V 4A Power MOSFET

Datasheet

V_{DSS}	45V
$R_{DS(on)}$ (Max.)	53mΩ
I_D	4A
P_D	1.5W

●Outline

TSMT8



●Features

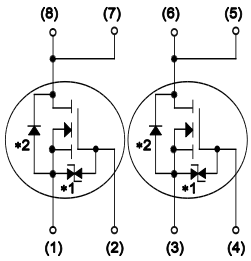
1) Low on - resistance.

2) Built-in G-S Protection Diode.

3) Small Surface Mount Package (TSMT8).

4) Pb-free lead plating ; RoHS compliant

●Inner circuit



(1) Tr1 Source (5) Tr2 Drain
(2) Tr1 Gate (6) Tr2 Drain
(3) Tr2 Source (7) Tr1 Drain
(4) Tr2 Gate (8) Tr1 Drain

∗1 ESD PROTECTION DIODE
∗2 BODY DIODE

●Application

DC/DC converters

●Packaging specifications

Type	Packaging	Taping
	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	3,000
	Taping code	TR
	Marking	K21

●Absolute maximum ratings(T_a = 25°C) <It is the same ratings for the Tr1 and Tr2>

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	45	V
Continuous drain current	I_D *1	±4	A
Pulsed drain current	$I_{D,pulse}$ *2	±12	A
Gate - Source voltage	V_{GSS}	±20	V
Power dissipation	P_D *3	1.5	W / total
		1.25	W / element
	P_D *4	0.55	W / total
Junction temperature	T_j	150	°C
Range of storage temperature	T_{stg}	−55 to +150	°C

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	R_{thJA} *3	-	-	83.3	°C/W
	R_{thJA} *4	-	-	227	°C/W

●Electrical characteristics(T_a = 25°C) ,unless otherwise specified

<It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 1mA	45	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	I_D=1mA referenced to 25°C	-	42	-	mV/°C
Zero gate voltage drain current	I_{DSS}	V_{DS} = 45V, V_{GS} = 0V	-	-	1	μA
Gate - Source leakage current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V	-	-	±10	μA
Gate threshold voltage	$V_{GS\ (th)}$	V_{DS} = 10V, I_D = 1mA	1.0	-	2.5	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{(GS)th}}{\Delta T_j}$	I_D=1mA referenced to 25°C	-	–4.2	-	mV/°C
Static drain - source on - state resistance	$R_{DS(on)}$ *5	V_{GS}=10V, I_D=4A	-	38	53	mΩ
		V_{GS}=4.5V, I_D=4A	-	48	67	
		V_{GS}=4.0V, I_D=4A	-	53	75	
		V_{GS}=10V, I_D=4A, T_j=125°C	-	66	93	
Gate input resistannce	R_G	f = 1MHz, open drain	-	6	-	Ω
Transconductance	g_{fs} *5	V_{DS}=10V, I_D=4A	2.0	6.6	-	S

*1 Limited only by maximum temperature allowed.

*2 Pw ≤ 10μs, Duty cycle ≤ 1%

*3 Mounted on a ceramic board (30×30×0.8mm)

*4 Mounted on a FR4 (20×20×0.8mm)

*5 Pulsed

●Electrical characteristics(T_a = 25°C)

<It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	V_{GS} = 0V	-	460	-	pF
Output capacitance	C_{oss}	V_{DS} = 10V	-	110	-	
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	55	-	
Turn - on delay time	$t_{d(on)}$ *5	$V_{DD} \simeq$ 25V, V_{GS} = 10V	-	9	-	ns
Rise time	t_r *5	I_D = 2A	-	25	-	
Turn - off delay time	$t_{d(off)}$ *5	R_L = 12.5Ω	-	30	-	
Fall time	t_f *5	R_G = 10Ω	-	7	-	

●Gate Charge characteristics(T_a = 25°C)

<It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g *5	$V_{DD} \simeq$ 25V, I_D=4A V_{GS} = 5V	-	5.4	-	nC
		$V_{DD} \simeq$ 25V, I_D=4A V_{GS} = 10V	-	10	-	
Gate - Source charge	Q_{gs} *5	$V_{DD} \simeq$ 25V, I_D=4A V_{GS} = 5V	-	2.0	-	
Gate - Drain charge	Q_{gd} *5		-	1.6	-	

●Body diode electrical characteristics (Source-Drain)(T_a = 25°C)

<It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Inverse diode continuous, forward current	I_S *1	T_a = 25°C	-	-	1	A
Forward voltage	V_{SD} *5	V_{GS} = 0V, I_s = 4A	-	-	1.2	V

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

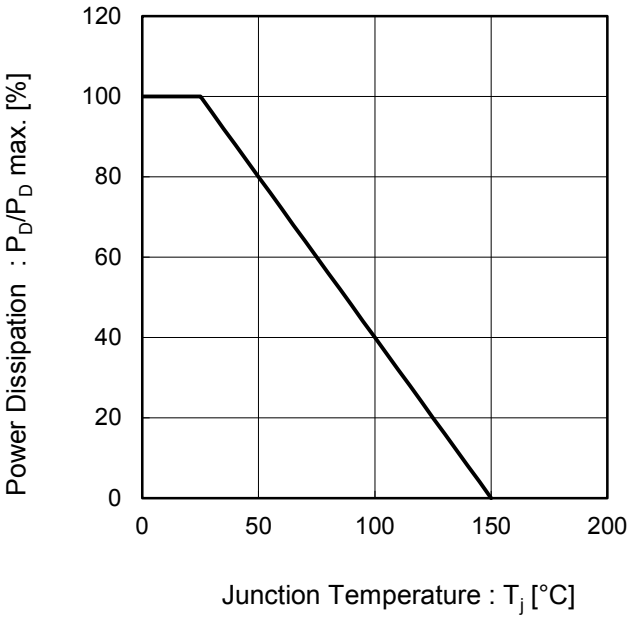


Fig.2 Maximum Safe Operating Area

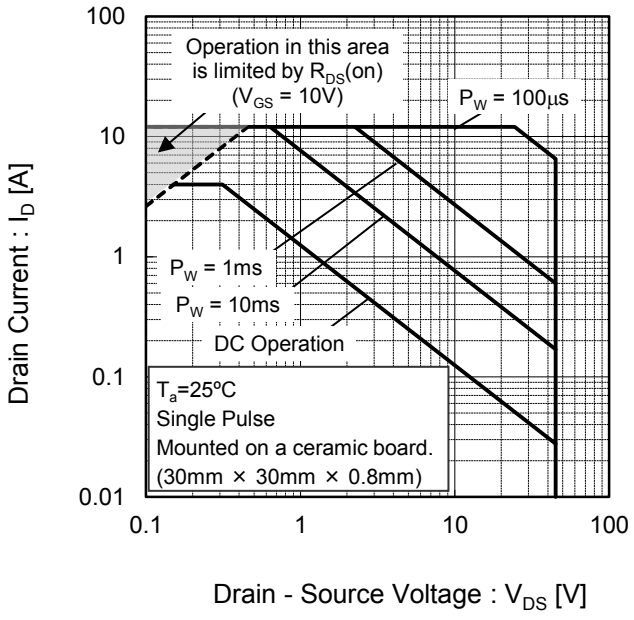


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

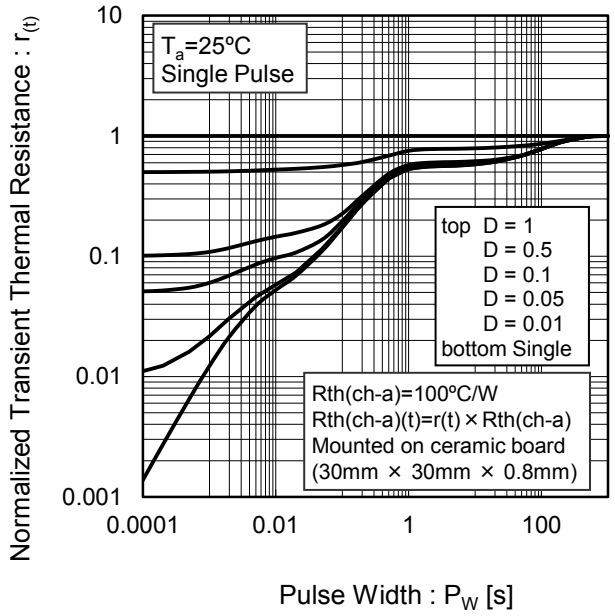
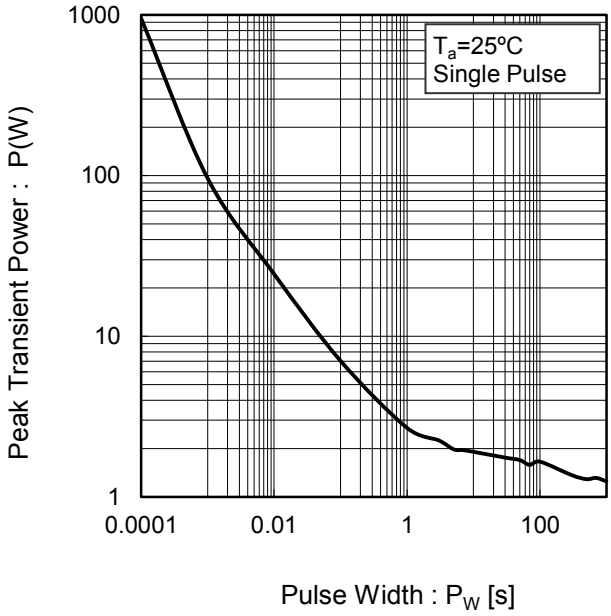


Fig.4 Single Pulse Maximum Power dissipation



●Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

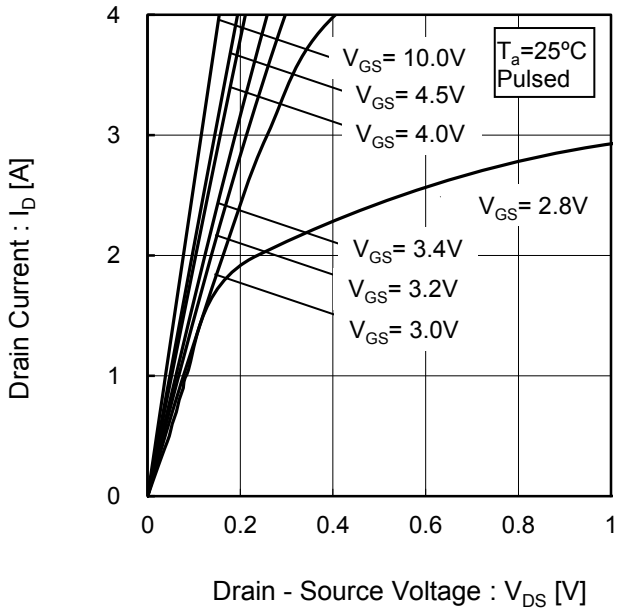


Fig.6 Typical Output Characteristics(II)

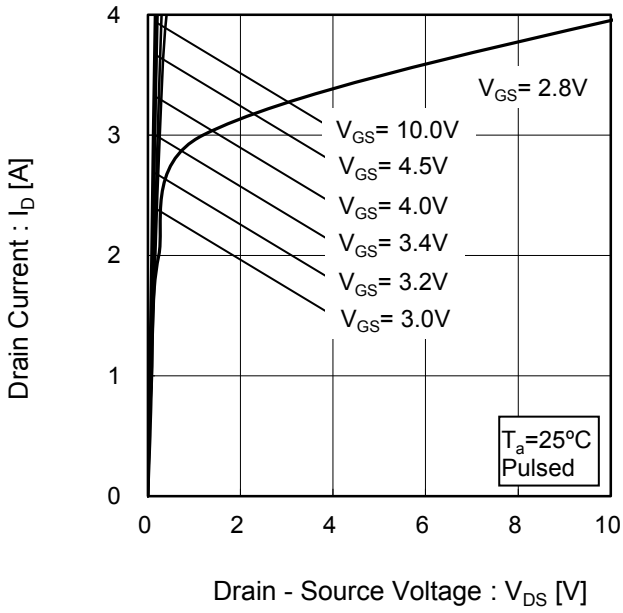


Fig.7 Breakdown Voltage vs. Junction Temperature

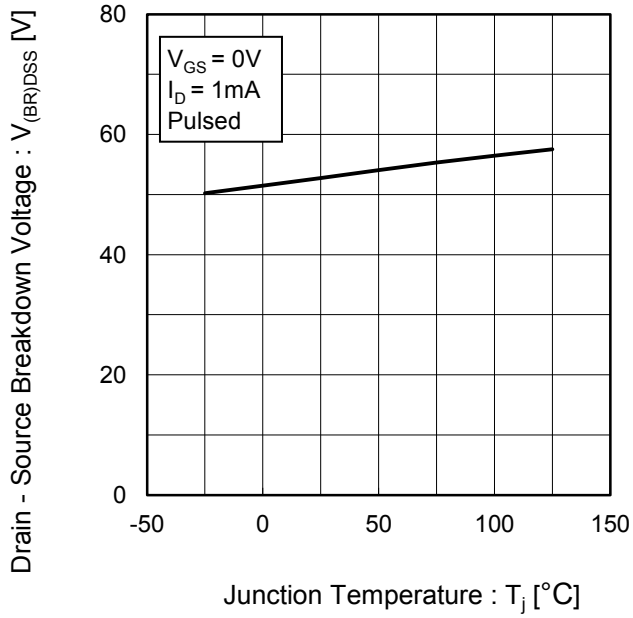
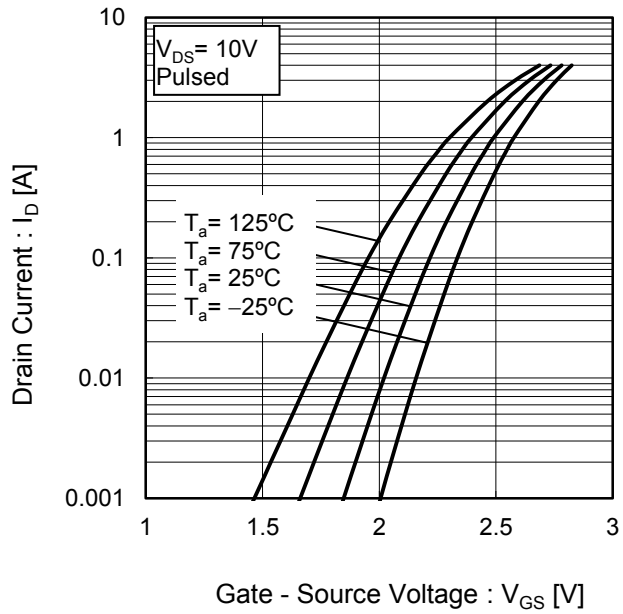


Fig.8 Typical Transfer Characteristics



●Electrical characteristic curves

Fig.9 Gate Threshold Voltage vs. Junction Temperature

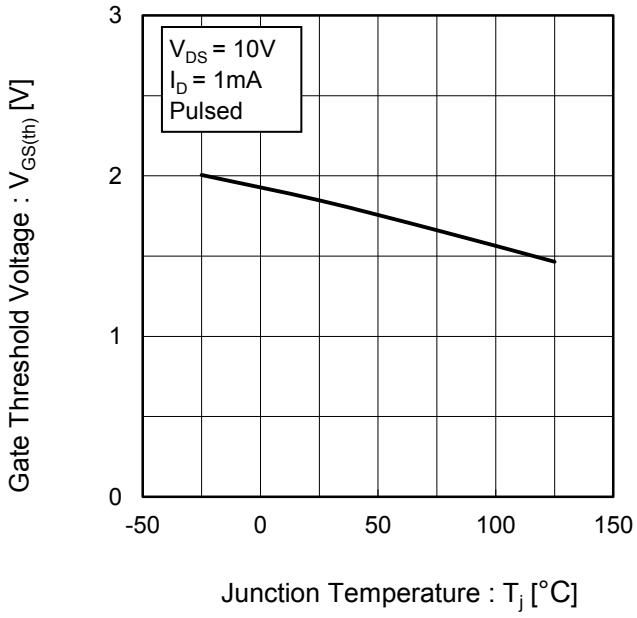


Fig.10 Transconductance vs. Drain Current

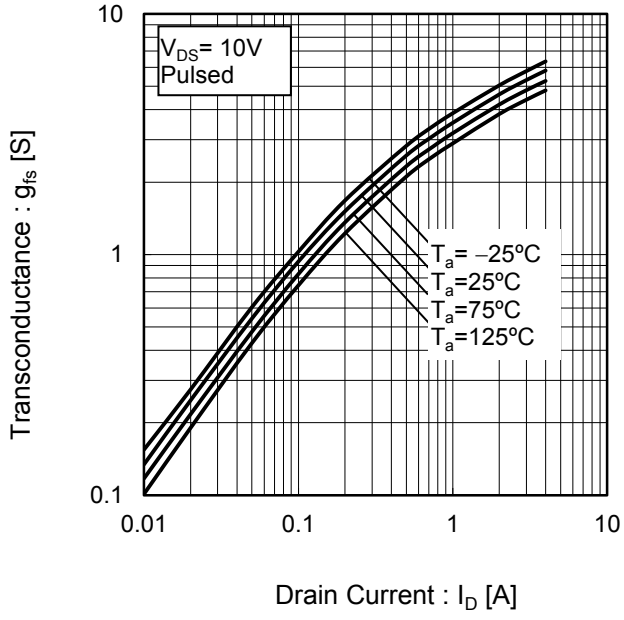


Fig.11 Drain CurrentDerating Curve

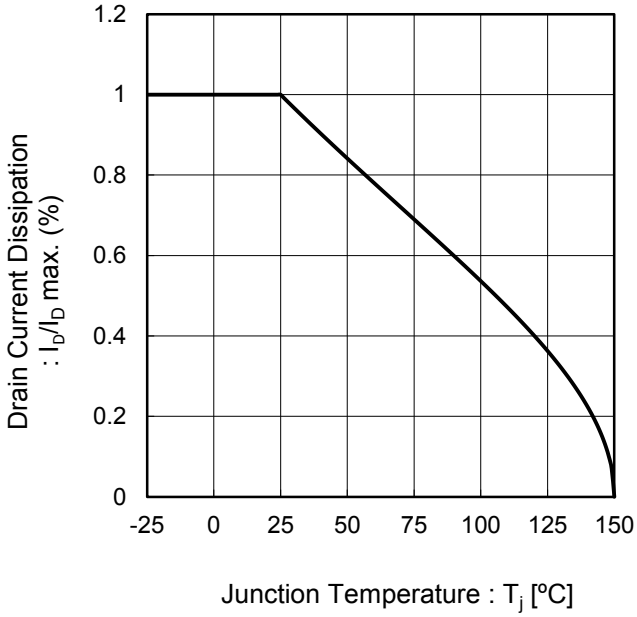
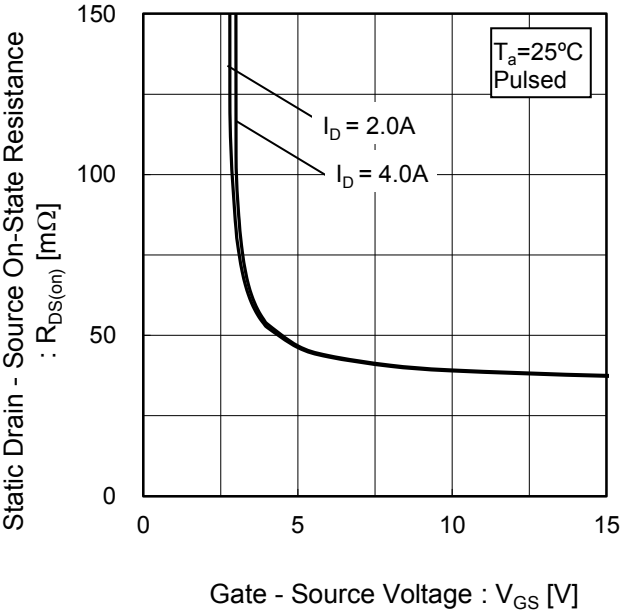


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



●Electrical characteristic curves

Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(I)

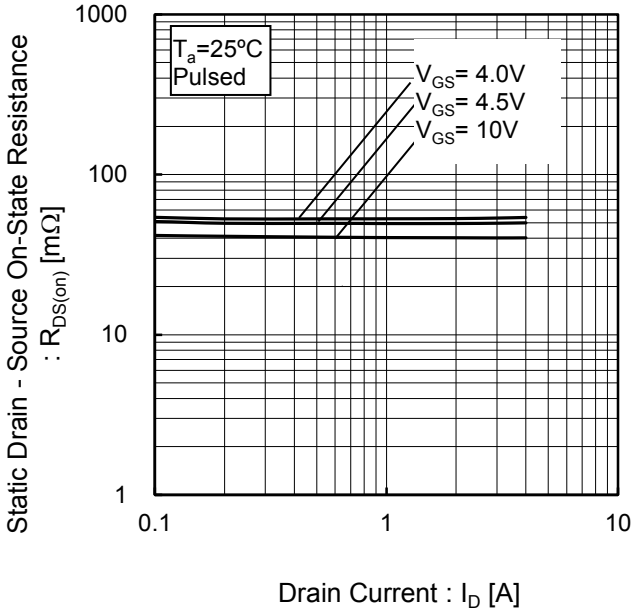


Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature

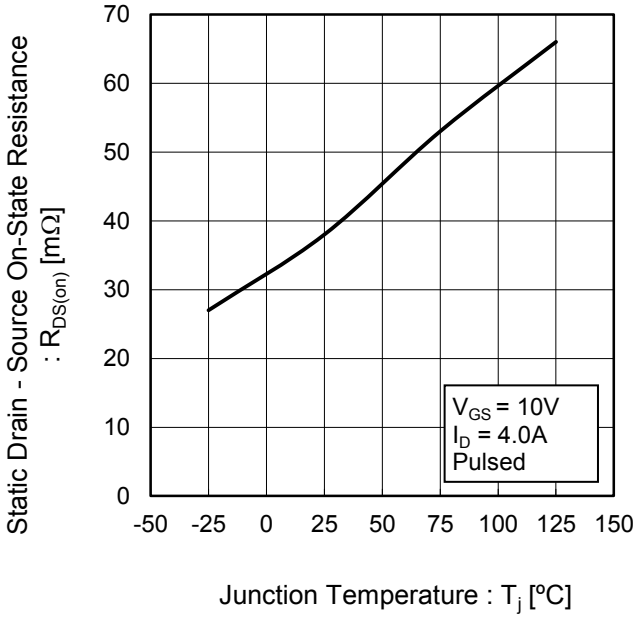


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

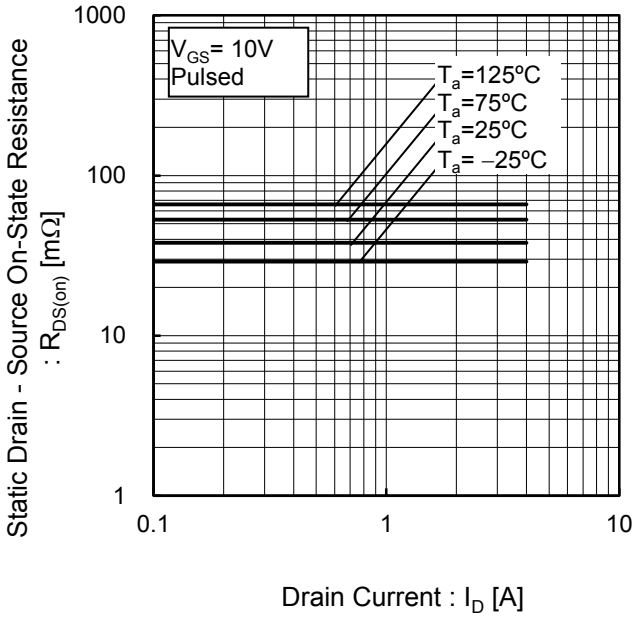
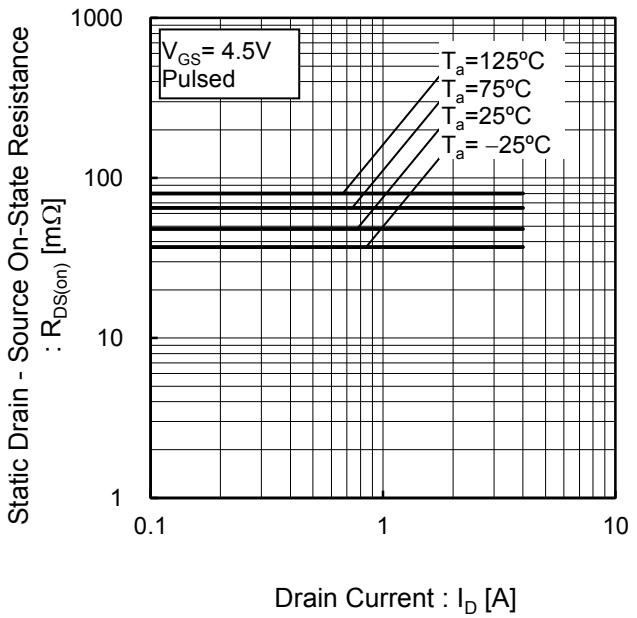


Fig.16 Static Drain-Source On-State Resistance vs. Drain Current(III)



●Electrical characteristic curves

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV)

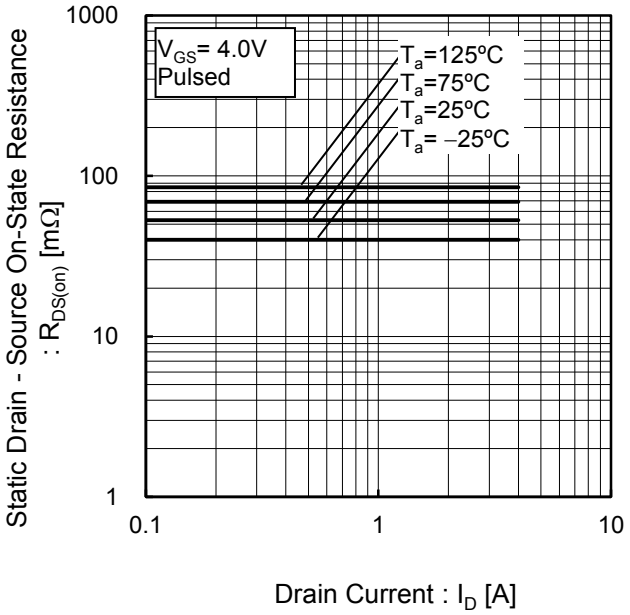


Fig.18 Typical Capacitance vs. Drain - Source Voltage

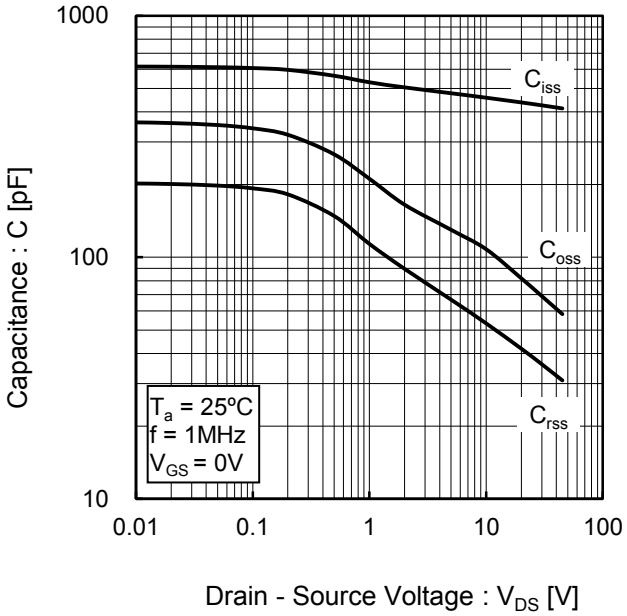


Fig.19 Switching Characteristics

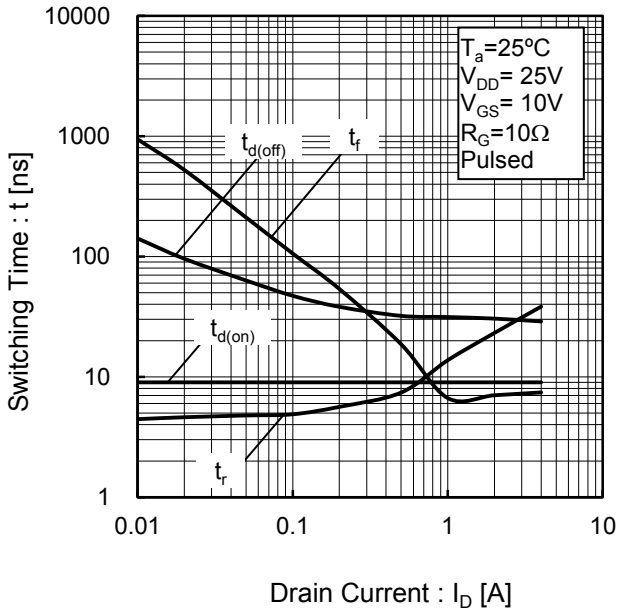
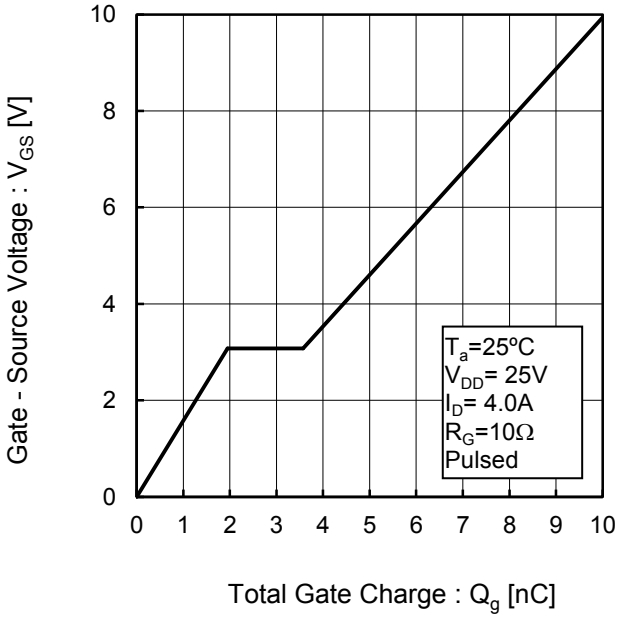
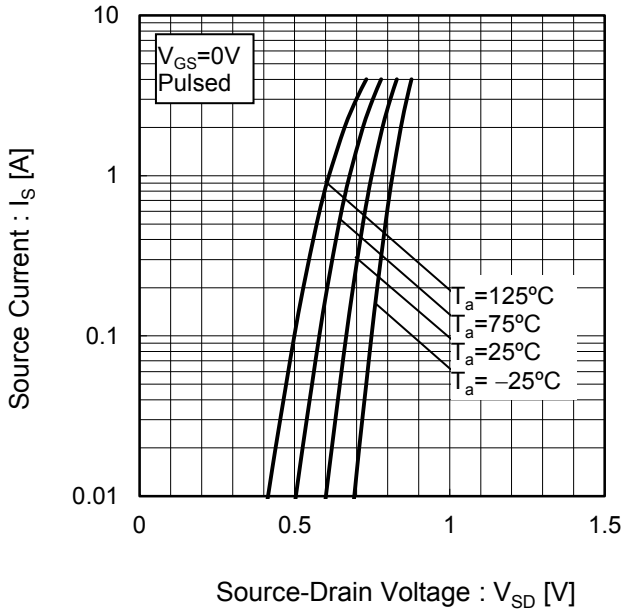


Fig.20 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.21 Source Current
vs. Source Drain Voltage



●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

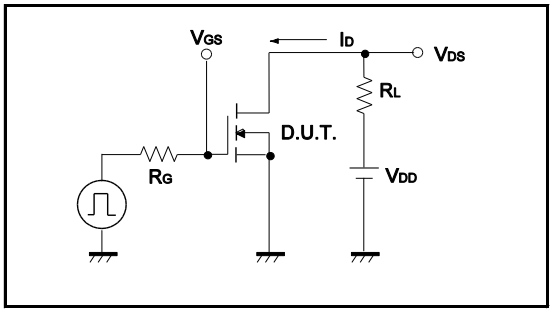


Fig.1-2 Switching Waveforms

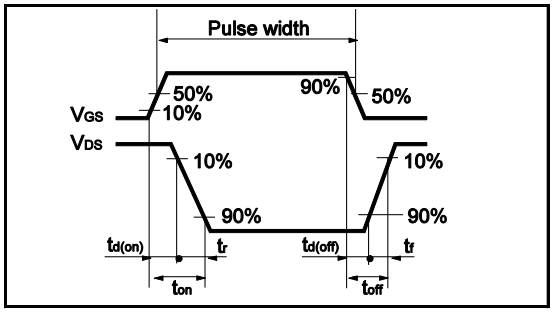


Fig.2-1 Gate Charge Measurement Circuit

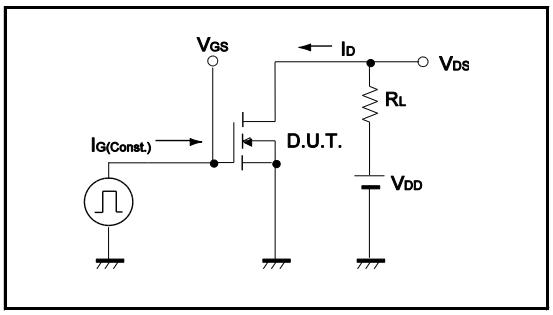
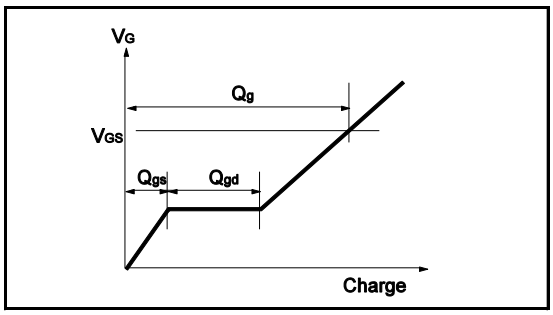
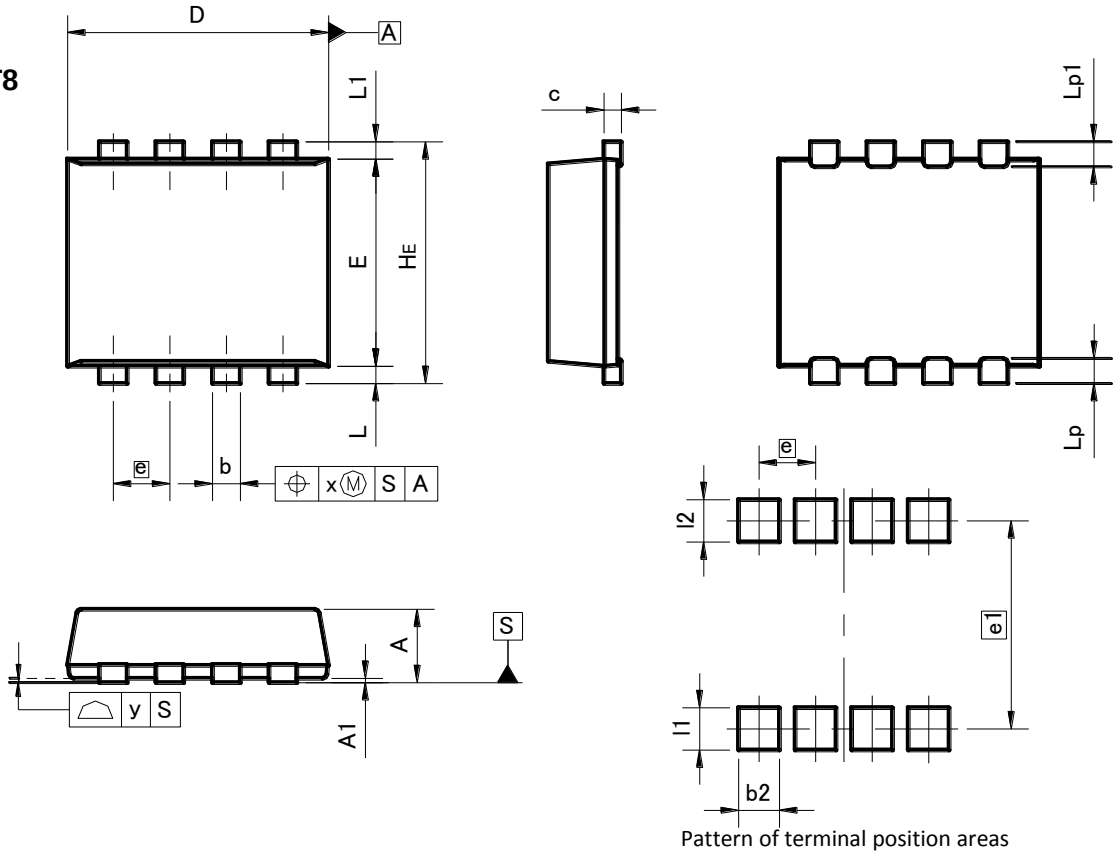


Fig.2-2 Gate Charge Waveform



●**Dimensions** (Unit : mm)

TSMT8



Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.75	0.85	0.030	0.033
A1	0.00	0.05	0.000	0.002
b	0.27	0.37	0.011	0.015
c	0.12	0.22	0.005	0.009
D	2.90	3.10	0.114	0.122
E	2.30	2.50	0.091	0.098
e	0.65		0.026	
HE	2.70	2.90	0.106	0.114
L	0.10	0.30	0.004	0.012
L1	0.10	0.30	0.004	0.012
Lp	0.19	0.39	0.007	0.015
Lp1	0.19	0.39	0.007	0.015
x	−	0.10	−	0.004
y	−	0.10	−	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	−	0.47	−	0.019
e1	2.41		0.095	
l1	−	0.49	−	0.019
l2	−	0.49	−	0.019

Dimension in mm / inches

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7) The Products specified in this document are not designed to be radiation tolerant.

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